

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
100V	110m Ω @ $V_{GS} = 10\text{V}$	3.6A
	122m Ω @ $V_{GS} = 6.0\text{V}$	3.4A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features and Benefits

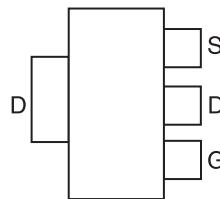
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

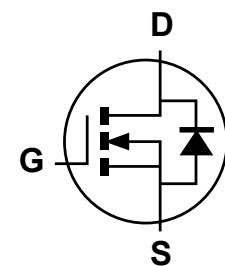
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.112 grams (Approximate)



Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

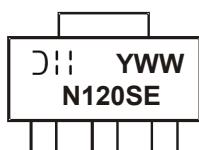
Part Number	Qualification	Case	Packaging
DMN10H120SE-13	Standard	SOT223	2,500/Tape & Reel

Notes:

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

SOT223



DII = Manufacturer's Marking
 N120SE = Marking Code
 YWW = Date Code Marking
 Y or Y = Year (ex: 5 = 2015)
 WW = Week (01 - 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	3.6 2.9	A
Pulsed Drain Current (10 μs pulse, duty cycle $\leq 1\%$)			I_{DM}	16	A
Maximum Body Diode Continuous Current (Note 6)			I_S	2.5	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P_D	1.3	W
	(Note 6)		2.1	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	94	°C/W
	(Note 6)		58	
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	8.2	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(\text{th})}$	1.5	2.6	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	77	110	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 3.3\text{A}$
		—	84	122		$V_{GS} = 6.0\text{V}, I_D = 3.0\text{A}$
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	$V_{GS} = 0\text{V}, I_S = 3.2\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	549	—	pF	$V_{DS} = 50\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	41	—		
Reverse Transfer Capacitance	C_{rss}	—	19	—		
Gate Resistance	R_g	—	1.6	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	10	—	nC	$V_{DS} = 50\text{V}, I_D = 3.3\text{A}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	5.2	—		
Gate-Source Charge	Q_{gs}	—	2.3	—		
Gate-Drain Charge	Q_{gd}	—	2.6	—		
Turn-On Delay Time	$t_{D(\text{on})}$	—	3.8	—	nS	$V_{DD} = 50\text{V}, V_{GS} = 10\text{V}, R_G = 6.0\Omega, I_D = 3.3\text{A}$
Turn-On Rise Time	t_r	—	1.8	—		
Turn-Off Delay Time	$t_{D(\text{off})}$	—	11	—		
Turn-Off Fall Time	t_f	—	2.5	—		
Reverse Recovery Time	t_{rr}	—	21	—	nS	$V_{GS} = 0\text{V}, I_S = 1.1\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{rr}	—	17	—		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

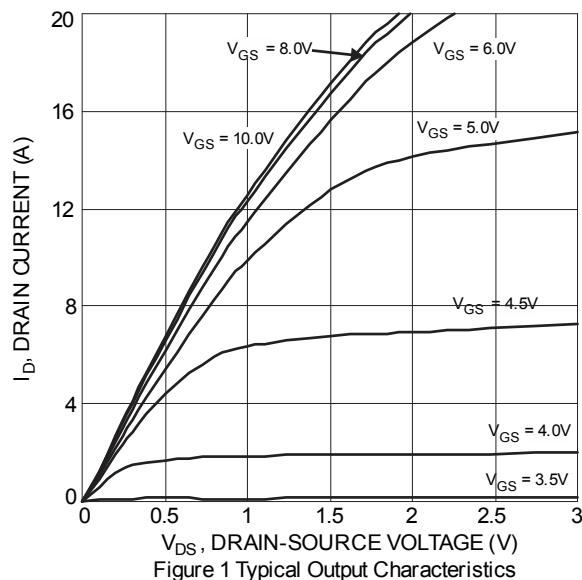


Figure 1 Typical Output Characteristics

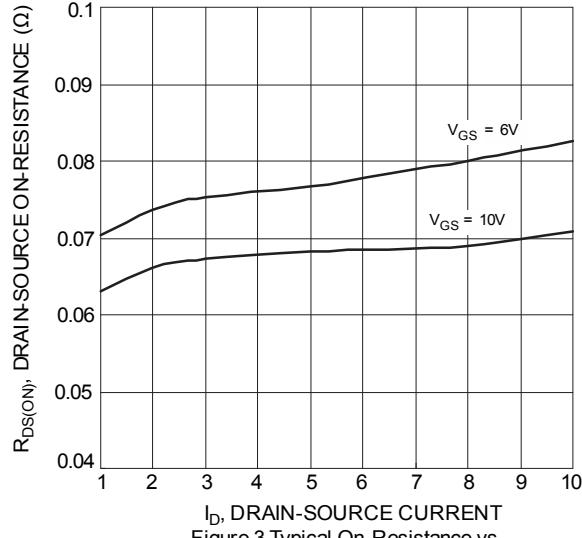


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

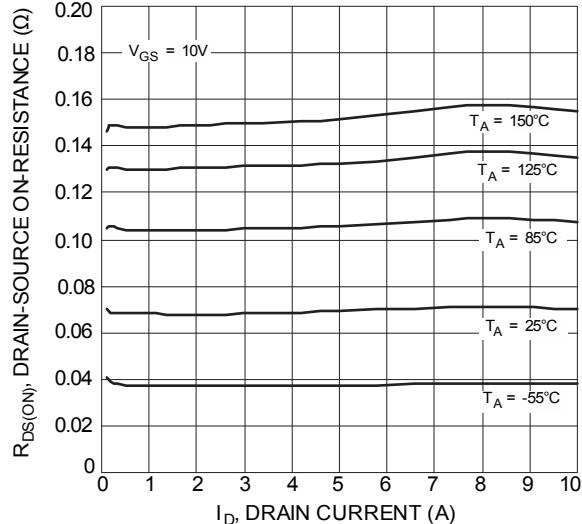


Figure 5 Typical On-Resistance vs.
Drain Current and Temperature

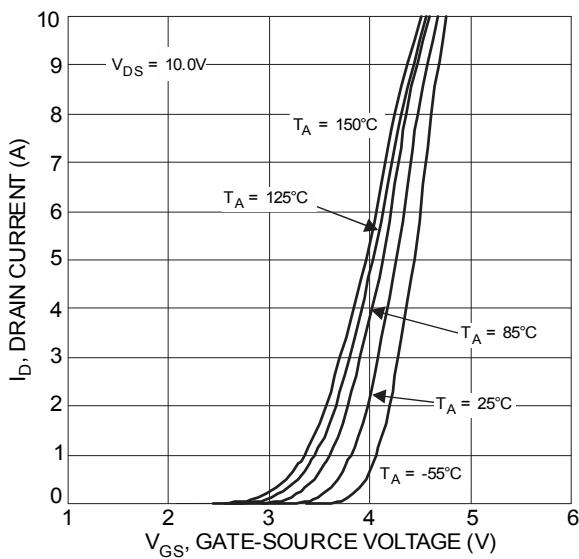


Figure 2 Typical Transfer Characteristics

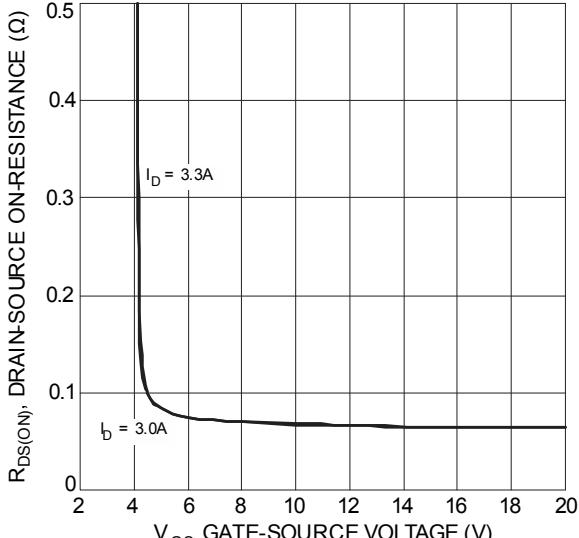


Figure 4 Typical Transfer Characteristics

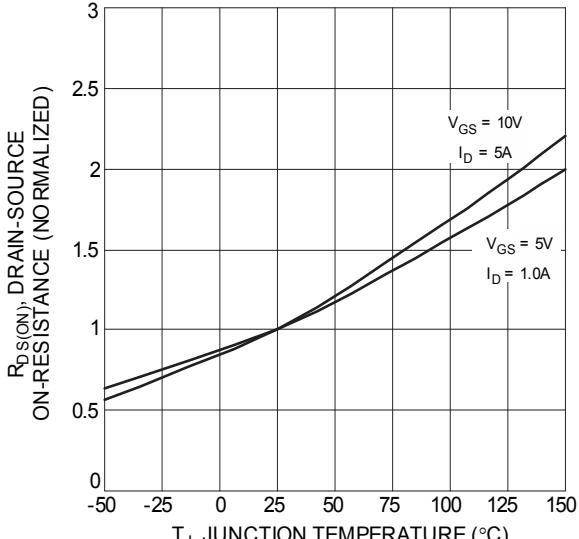
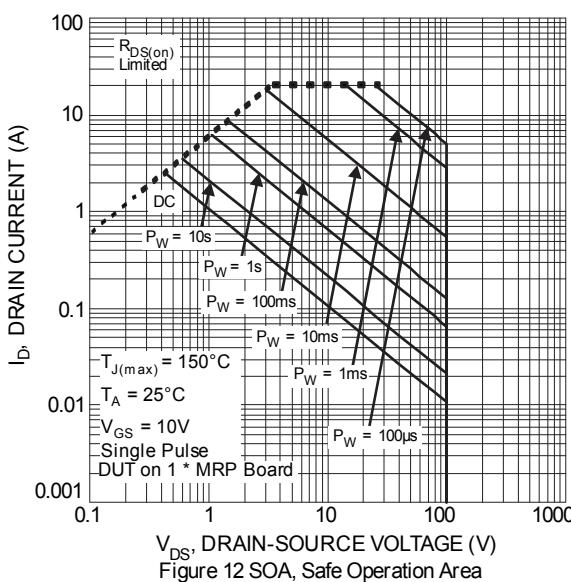
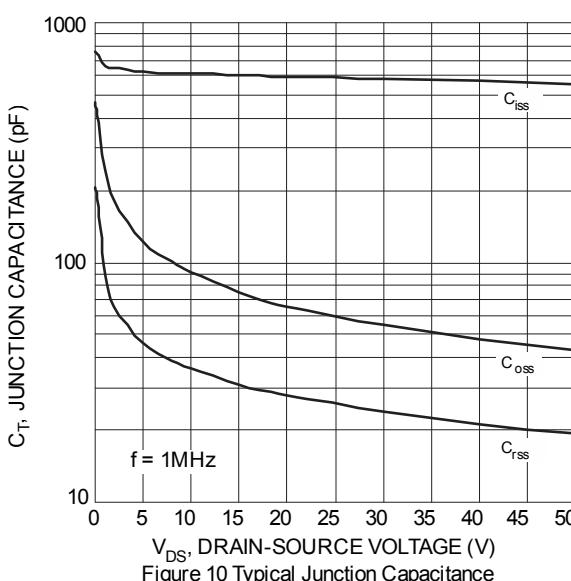
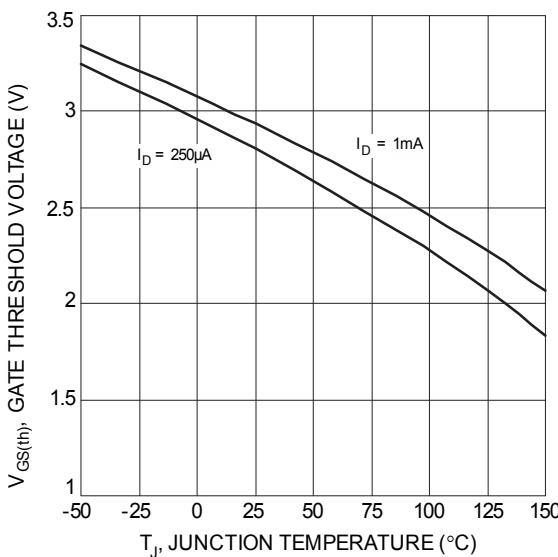
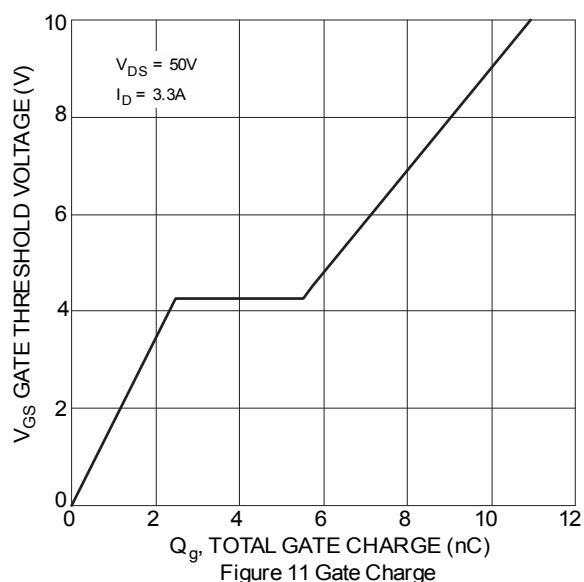
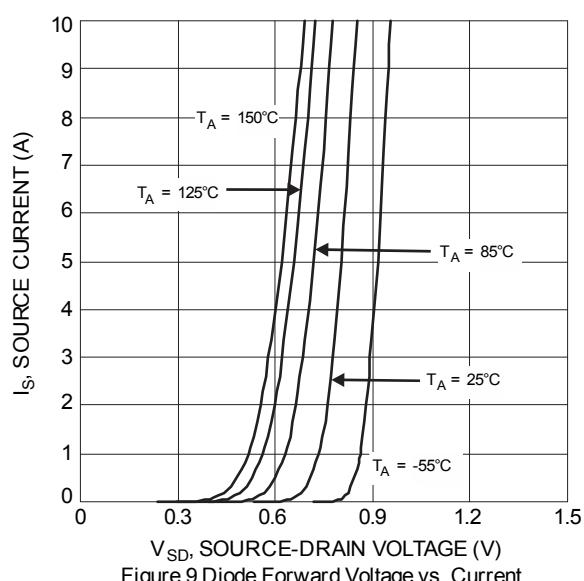
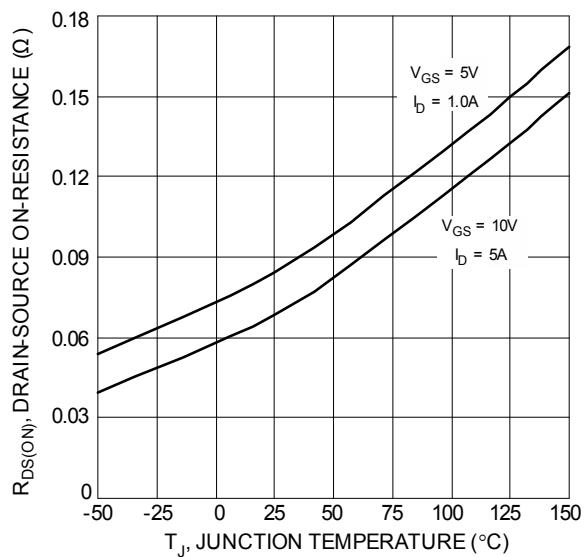


Figure 6 On-Resistance Variation with Temperature



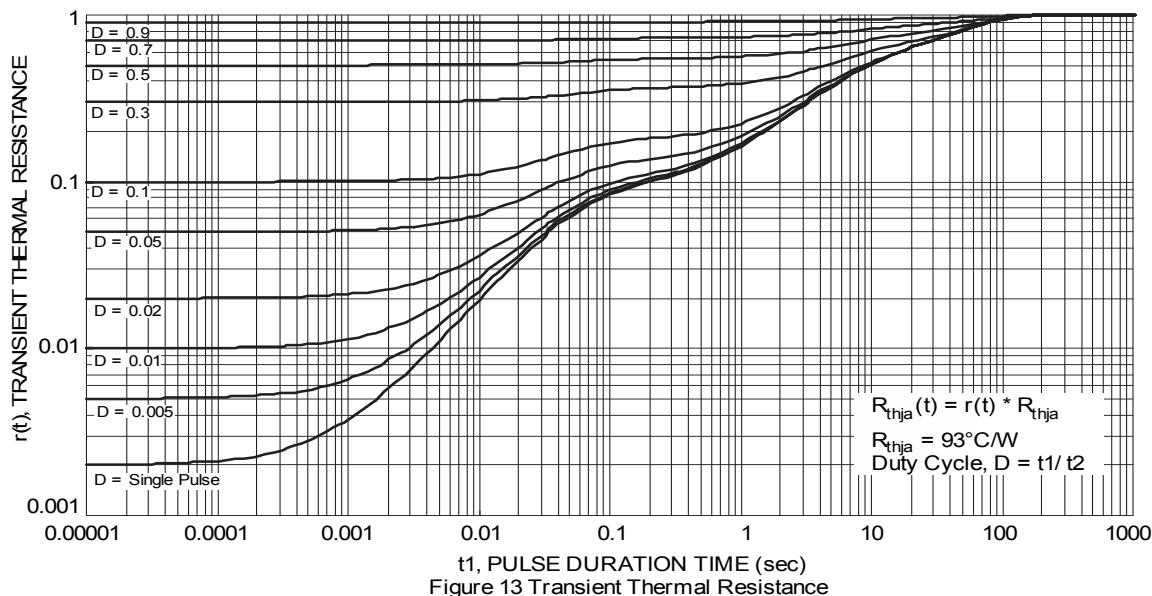
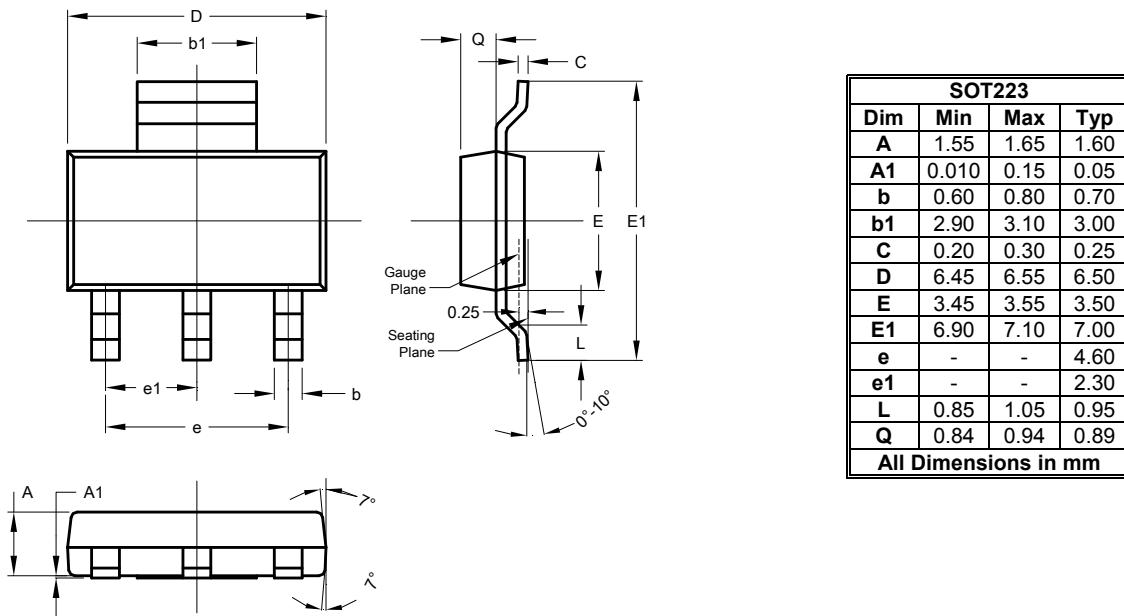


Figure 13 Transient Thermal Resistance

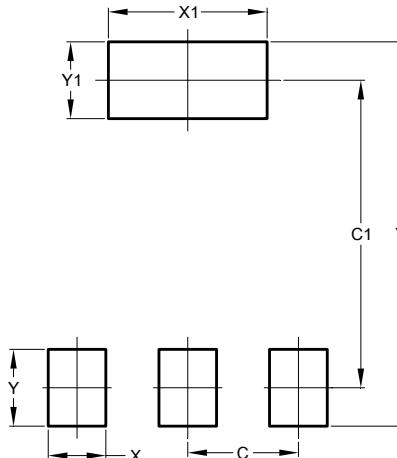
Package Outline Dimensions & Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8.00

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